

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	176	takagi near hideo.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	6	enda near takayuki.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	0	umetsu near myuki.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	1972	438/257.ccls.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	280	(charge near storage near film)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
6	BRS	L6	17	(eras\$3) near15 (charge near storage near film)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L7	2	(eras\$3) near15 (charge near storage near film) near15 (hydrogen)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
8	BRS	L8	2	(eras\$3) near15 (charge near storage near film) same (hydrogen)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	5	(eras\$3) near15 (charge near storage near film) and (hydrogen)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
10	BRS	L11	2	(eras\$3) near15 (charge near storage) near15 (hydrogen)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
11	BRS	L12	2	(eras\$3) near15 (charge near storage) same (hydrogen)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
12	BRS	L10	39	(eras\$3) near15 (charge near storage) and (hydrogen)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
13	BRS	L13	2	(eras\$3) near15 (charge near storage) and (plasma near hydrogen)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
14	BRS	L14	41	(charge near storage) and (plasma near hydrogen)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
15	BRS	L15	11	(reduc\$3 or remov\$3 or delet\$3 or eras\$3) near15 (charge near3 storage) and (plasma near hydrogen)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
16	BRS	L16	32	(reduc\$3 or remov\$3 or delet\$3 or eras\$3) near15 (charge near3 storage) and (plasma near5 hydrogen)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
17	BRS	L18	2	(reduc\$3 or remov\$3 or delet\$3 or eras\$3) near15 (charge near3 storage) and (plasma near3 hydrogen) near25 (contact or hole)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
18	BRS	L17	30	(reduc\$3 or remov\$3 or delet\$3 or eras\$3) near15 (charge near3 storage) and (plasma near3 hydrogen)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
19	BRS	L19	11	(eras\$3) near15 (charge near3 storage) and (plasma near10 hydrogen)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
20	BRS	L20	76	(eras\$3) near15 (charge) and (plasma near10 hydrogen)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
21	BRS	L21	7	(eras\$3) near15 (charge) and (plasma near1 hydrogen)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
22	BRS	L22	76	(eras\$3) near15 (charge) and (plasma near10 hydrogen)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
23	BRS	L23	45	(eras\$3) near5 (charge) and (plasma near10 hydrogen)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
24	BRS	L24	76	(eras\$3) near15 (charge) and (plasma near10 hydrogen)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
25	BRS	L25	3	(eras\$3) near15 (charge) and (plasma near10 hydrogen) near15 (anneal\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	U	1	Document ID	Title
1			US 20040145316 A1	Plasma display panel and manufacturing method therefor
2			US 20040110390 A1	Semiconductor memory device and method of fabricating the same
3			US 6551867 B1	Non-volatile semiconductor memory device and method for manufacturing the same
4			US 5849446 A	Light receiving member having a surface protective layer with a specific outermost surface and process for the production thereof
5			US 5264724 A	Silicon nitride for application as the gate dielectric in MOS devices
6			US 4962065 A	Annealing process to stabilize PECVD silicon nitride for application as the gate dielectric in MOS devices
7			US 20040110390 A	Semiconductor memory device production comprises subjecting charge storage film to hydrogen plasma treatment after its formation to erase electric charge stored in charge storage film